

Listing of Claims:

Claims 1 - 22 (canceled)

23. (currently amended) A method for fabricating multilevel metal interconnections having low dielectric constant insulators on a substrate comprising the steps of:

providing first metal lines, formed over said substrate;

coating a layer of low dielectric constant insulating material on and in between said metal lines;

curing the low dielectric constant material at 400°C;

depositing by plasma enhanced chemical vapor deposition a [[thin]] layer of silicon nitride, an adhesion promoter and stabilizing material, to a thickness of between approximately 200 to 500 Angstroms, on the low dielectric constant material;

depositing by plasma enhanced chemical vapor deposition a silicon oxide cap layer on the adhesion promoter and over the low dielectric constant material; and

planarizing the silicon oxide cap layer by chemical mechanical polish (CMP).

24. (previously presented) The method of claim 23, wherein said low dielectric constant material is spun on dielectric,

deposited to a thickness of about 4,000 to 12,000 Angstroms, with curing conditions at 400°C for 1 hr., in a nitrogen ambient gas flow from about 1 to 30 SLM, oxygen less than 10 ppm.

25. (currently amended) The method of claim 23, wherein said layer of adhesion promoter and stabilizer is a non-oxide compound, comprised of SiN, SiC, BC, BCN, BN, or spun on compounds.

Claim 26 (canceled)

27. (previously presented) The method of claim 23, wherein said silicon oxide cap layer is deposited by plasma enhanced chemical vapor deposition, to a thickness of between about 4,000 to 16,000 Angstroms.

Claims 28 - 41 (canceled)